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(54) Title (EN): METHOD FOR RECOVERING ELEMENTAL SILICON FROM CUTTING REMAINS

(54) Title (FR): PROCÉDÉ DE RÉCUPÉRATION DE SILICIUM ÉLÉMENTAIRE À PARTIR DE DÉBRIS DE DÉCOUPE

(57) Abstract:

(EN): This invention relates to a method for recovering elemental silicon cutting remains containing silicon particles, wherein the method comprises manufacturing solid anodes from the cutting remains, arranging one or more manufactured anode (s) in an electrolytic cell with a molten salt electrolyte and one or more cathode (s), and applying a potential difference between the one or more anode (s) and cathode (s) to obtain an oxidation of metallic silicon in the one or more anode (s), transportation of dissolved silicon in the electrolyte, and reduction of the dissolved silicon to a metallic phase at the one or more cathode (s).

(FR): Cette invention porte sur un procédé de récupération de débris de découpe de silicium élémentaire contenant des particules de silicium. Le procédé comprend la fabrication d'anodes solides à partir des débris de découpe, l'arrangement d'une ou plusieurs anodes fabriquées dans une cellule électrolytique avec un électrolyte et une ou plusieurs cathodes, et l'application d'une différence de potentiel entre une ou plusieurs anodes et une ou plusieurs cathodes afin d'obtenir une oxydation de silicium métallique

dans une ou plusieurs anodes, le transport de silicium dissous dans l'électrolyte, et la réduction du silicium dissous à une phase métallique au niveau d'une ou plusieurs cathodes.

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